## 10/002924

Number	Hits 0	Search Text	DB	Time stamp
	0			
	J	6730960.pn. and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode)	USPAT; US-PGPUB; EPO; JPO;	2004/10/22 11:24
2	0	6720221.pn. and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/22 11:25
3	0	6639835.pn. and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/22 11:25
4	0	6605961.pn. and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/22 11:25
5	0	6456535.pn. and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/22 11:26
6	0	6297103.pn. and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:26
7	0	@ad<20000228 and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode) and ("23" adj	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:33
8	0	same ("<2.5 adj volts") same erase) and (enhancement adj mode) and ("40" adj	USPAT; US-PGPUB; EPO; JPO;	2004/10/22
9	0	angstroms) @ad<20000228 and ((operating adj voltage) same ("<2.5 adj volts") same erase) and (enhancement adj mode) and ("<40" adj	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/22 11:32
10	0	angstroms) @ad<20000228 and ((operating adj voltage) same ("<2.5 adj volts")) and (enhancement adj mode) and ("<40" adj angstroms)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/22 11:32
11	0	<pre>@ad&lt;20000228 and ((operating adj voltage) same ("&lt;2.5 adj volts")) and (enhancement adj mode) and ("&lt;30" adj angstroms)</pre>	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:34
12	0	@ad<20000228 and ((operating adj voltage) same ("<2.5 adj volts")) and (enhancement adj mode) and ("<40" adj angstroms)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:36
13	0	@ad<20000228 and ((operating adj voltage) same ("<3.5 adj volts")) and (enhancement adj mode) and ("<35" adj angstroms)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22
14	0	<pre>@ad&lt;20000228 and ((operating adj voltage) same ("&lt;3.5 adj volts")) and (enhancement adj mode) and (("&lt;30" adj angstroms) same oxide)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:39
15	. 0	@ad<20000228 and ((operating adj voltage) same ("<3.5 adj volts")) and (enhancement adj mode) and (("<35" adj angstroms) same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:40
16	0	@ad<20000228 and ((operating adj voltage) same ("<3.5 adj volts")) and (enhancement adj mode) and (("<35" adj angstroms) same oxide) and (memory adj cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:41
17	o	@ad<20000228 and ((operating adj voltage) same ("<1.5 adj volts")) and (enhancement adj mode) and (("<25" adj angstroms) same oxide) and (memory adj cell) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 11:44

<u>1</u>		<u> </u>		
18	0	@ad<20000228 and ((operating adj voltage)	USPAT;	2004/10/22
İ		same ("<1.5 adj volts")) and (enhancement	US-PGPUB;	11:46
		adj mode) and (("<40" adj angstroms) same oxide) and (memory adj cell) and	EPO; JPO; DERWENT	
		transistor	DERWENT	
19	0	@ad<20000228 and (enhancement adj mode)	USPAT;	2004/10/22
		and (("<40" adj angstroms) same oxide)	US-PGPUB;	11:50
		and (memory adj cell) and transistor	EPO; JPO;	
			DERWENT	
20	0	<pre>@ad&lt;20000228 and (enhancement adj mode)</pre>	USPAT;	2004/10/22
		and (("<25" adj angstroms) same oxide)	US-PGPUB;	11:53
		and (memory adj cell) and transistor and	EPO; JPO; DERWENT	
21	0	(floating adj gate) @ad<20000228 and (enhancement adj mode)	USPAT;	2004/10/22
21	O	and (("<40" adj angstroms) same oxide)	US-PGPUB;	11:55
		and (memory adj cell) and transistor and	EPO; JPO;	
		((floating adj gate) same erase same	DERWENT	
		("<3.5" volts))		
22	0	257/315,316.ccls and (memory adj cell)	USPAT;	2004/10/22
		and (oxide adj layer) and (floating adj	US-PGPUB;	11:58
		gate) and (dielectric adj layer) and	EPO; JPO;	
		(control adj gate) and ((oxide adj layer)	DERWENT	
23	5	same ("<50" adj angstroms)) 438/257,263,264,762,763.ccls. and (memory	USPAT;	2004/10/22
23	5	adj cell) and (floating adj gate) and	US-PGPUB;	12:04
		(dielectric adj layer) and (control adj	EPO; JPO;	
		gate) and ((oxide adj layer) same ("<45"	DERWENT	
		adj angstroms))	_	
24	0	438/257,263,264,762,763.ccls. and (memory	USPAT;	2004/10/22
		adj cell) and (floating adj gate) and	US-PGPUB;	12:05
-		(dielectric adj layer) and (control adj	EPO; JPO; DERWENT	
		gate) and ((oxide adj layer) same ("<45" adj angstroms)) and (enhancement adj	DEKWENI	
		p-channel adj transistor)		
25	О	438/257,263,264,762,763.ccls. and (memory	USPAT;	2004/10/22
		adj cell) and (floating adj gate) and	US-PGPUB;	12:06
		(dielectric adj layer) and (control adj	EPO; JPO;	
		gate) and ((oxide adj layer) same ("<45"	DERWENT	
		adj angstroms)) and (enhancement adj		
26	0	p-channel) and transistor 438/257,263,264,762,763.ccls. and (memory	USPAT;	2004/10/22
26	0	adj cell) and (floating adj gate) and	US-PGPUB;	12:07
		(dielectric adj layer) and (control adj	EPO; JPO;	12.07
		gate) and ((oxide adj layer) same ("<45"	DERWENT	
		adj angstroms)) and (enhancement adj		
		p-channel) and (transistor or memory		
		cell)		2004/10/22
27	0	438/257, 263, 264, 762, 763.ccls. and (memory	USPAT;	2004/10/22
		adj cell) and (floating adj gate) and (dielectric adj layer) and (control adj	US-PGPUB; EPO; JPO;	12:22
		gate) and ((oxide adj layer) same ("<45"	DERWENT	
		adj angstroms)) and (enhancement adj		
		p-channel) and (transistor or (memory adj		
		cell))		
28	0	438/257,263,264,762,763.ccls. and	USPAT;	2004/10/22
		(floating adj gate) and (dielectric adj	US-PGPUB;	12:16
	•	layer) and (control adj gate) and ((oxide	EPO; JPO;	
		adj layer) same ("<45" adj angstroms)) and (enhancement adj p-channel) and	DERWENT	
		(transistor or (memory adj cell))		
29	0	6720221.pn. and floating adj gate	USPAT;	2004/10/22
	Ĭ	· · · · · · · · · · · · · · · · · ·	US-PGPUB;	12:17
1		•	EPO; JPO;	
			DERWENT	
30	0	438/257, 258, 261, 263, 264, 762, 763, 275, 283.cc		2004/10/22
		and (memory adj cell) and (floating adj	US-PGPUB;	13:06
		gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer)	EPO; JPO; DERWENT	1
		same ("<45" adj angstroms)) and	DEVACAT	
			1	1
		<pre>(enhancement adj p-channel) and (transistor or (memory adj cell))</pre>	i	

•				
31	0	(memory adj cell) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer)	USPAT; US-PGPUB; EPO; JPO;	2004/10/22 13:06
		same ("<45" adj angstroms)) and (enhancement adj p-channel) and (transistor or (memory adj cell))	DERWENT	
_	790596	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	USPAT; US-PGPUB; EPO; JPO;	2004/10/21
-	1819	memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10 14:38
-	53	floating adj gate and dielectric adj layer and control adj gate) and oxide adj	USPAT; US-PGPUB; EPO; JPO;	2003/07/11
_	791060	layer with "50" adj angstroms memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control gate	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/10
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 adj	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:02
_	43	floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and .25 or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/13
-	0	quarter adj micron adj gate (memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:04
-	15	•	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.25 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/11 19:28
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and oxide adj layer with "50" adj angstroms and (.18 or quarter) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12
-	0		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.18) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.15) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(memory adj cell and oxide adj layer and floating adj gate and dielectric adj layer and control adj gate) and (.1) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:33
-	0	(.1) adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/12 11:34

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				· .
_	0	(.18) adj micron	USPAT;	2003/07/12
	-		US-PGPUB;	11:34
			EPO; JPO; DERWENT	
_	o	(.25) adj micron	USPAT;	2003/07/12
	ľ	(.23) adj micron	US-PGPUB;	11:34
		·	EPO; JPO;	
		•	DERWENT	
_	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:35
		layer and control adj gate) and (.25) adj	EPO; JPO;	
	1.5	micron (memory adj cell and oxide adj layer and	DERWENT	2003/07/12
-	15	floating adj gate and dielectric adj	USPAT; US-PGPUB;	11:36
•		layer and control adj gate) and (.25 or	EPO; JPO;	11.55
		quarter) adj micron	DERWENT	
_	0	(memory adj cell and oxide adj layer and	USPAT;	2003/07/12
		floating adj gate and dielectric adj	US-PGPUB;	11:36
		layer and control adj gate) and (.25) adj	EPO; JPO;	ļ
		micron	DERWENT	0000/07/10
-	43	438/257.CCLS. AND (memory adj cell and	USPAT;	2003/07/13
		oxide adj layer and floating adj gate and dielectric adj layer and control adj	US-PGPUB; EPO; JPO;	10:23
		gate) and oxide adj layer with "50" adj	DERWENT	
		angstroms and .25 or quarter adj micron		
		adj gate		
-	43	257/315,316.CCLS. AND 438/257.CCLS. AND	USPAT;	2003/07/13
		(memory adj cell and oxide adj layer and	US-PGPUB;	16:26
		floating adj gate and dielectric adj	EPO; JPO;	-
		layer and control adj gate) and oxide adj	DERWENT	
Ì		layer with "50" adj angstroms and .25 or quarter adj micron adj gate		
1_	48	memory adj cell and oxide adj layer and	USPAT;	2003/11/13
	40	floating adj gate and dielectric adj	US-PGPUB;	12:16
		layer and control adj gate and oxide adj	EPO; JPO;	
ļ.		layer with "50" adj angstroms and .25 or	DERWENT	
		quarter adj micron adj gate		/
-	1797	memory adj cell and oxide adj layer and	USPAT;	2003/11/13
		floating adj gate and dielectric adj	US-PGPUB; EPO; JPO;	12:08
		layer and control adj gate and oxide adj layer and "50" adj angstroms and .25 or	DERWENT	
		quarter adj micron		
_	0	l Toronto de la companya de la comp	USPAT;	2003/11/13
		and (floating adj gate) and (dielectric	US-PGPUB;	12:22
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("50" adj	DERWENT	
		angstroms) and (.25 or quarter adj micron		
_	57	adj gate))   (memory adj cell) and (oxide adj layer)	USPAT;	2003/11/13
	1	and (floating adj gate) and (dielectric	US-PGPUB;	18:04
		adj layer) and (control adj gate) and	EPO; JPO;	
		((oxide adj layer) with ("50" adj	DERWENT	
		angstroms))	HCD2m	2004/10/22
_	0	257/315,316.ccls and (memory adj cell)	USPAT; US-PGPUB;	2004/10/22
	1	and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and	EPO; JPO;	11.57
	1	(control adj gate) and ((oxide adj layer)	DERWENT	
		with ("50" adj angstroms))		
-	9	438/264,762,763.ccls. and (memory adj	USPAT;	2003/11/13
		cell) and (oxide adj layer) and (floating	US-PGPUB;	18:01
	1	adj gate) and (dielectric adj layer) and	EPO; JPO;	
	L	(control adj gate) and ((oxide adj layer)	DERWENT	
1_	0	with ("50" adj angstroms)) 438/264,762,763.ccls. and (memory adj	USPAT;	2003/11/29
1		cell) and (oxide adj layer) and (floating	US-PGPUB;	16:04
		adj gate) and (dielectric adj layer) and	EPO; JPO;	
		(control adj gate) and ((oxide adj layer)	DERWENT	
		with ("23" adj angstroms))		
-	0	6515328.pn. and (p adj channel)	USPAT;	2003/11/13
			US-PGPUB;	17:41
			EPO; JPO; DERWENT	
I	1		DEVMUNT_	

-	0	6515328.pn. and (p adj channel or	USPAT;	2003/11/13
		positiv\$3 adj dop\$3)	US-PGPUB;	17:43
			EPO; JPO;	
			DERWENT	
-	0		USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:44
			EPO; JPO;	
		5050011	DERWENT	2002/11/12
-	0		USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:45
			EPO; JPO; DERWENT	
	_	5869370.pn. and ((p adj channel) or	USPAT;	2003/11/13
_		(positiv\$3 adj dop\$3))	US-PGPUB;	17:46
		(positivas adj dopas))	EPO; JPO;	17.10
			DERWENT	
_	ا ا	6515328.pn. and ((p adj channel) or	USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:46
		(pobletivo daj dopto))	EPO; JPO;	
			DERWENT	
l _	l n	6383939.pn. and ((p adj channel) or	USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:47
			EPO; JPO;	
			DERWENT	
. <u>-</u>	0	6316316.pn. and ((p adj channel) or	USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:47
			EPO; JPO;	
			DERWENT	
-	1		USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:48
			EPO; JPO;	
			DERWENT	
-	0		USPAT;	2003/11/13
		(positiv\$3 adj dop\$3))	US-PGPUB;	17:48
İ			EPO; JPO;	
			DERWENT	0000/11/10
-	0		USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB;	17:49
		`	EPO; JPO;	
		5050211	DERWENT USPAT;	2003/11/13
-	0		US-PGPUB;	17:49
		(positiv\$3 same dop\$3))	EPO; JPO;	17.49
			DERWENT	
	0	5869370.pn. and ((p adj channel) or	USPAT;	2003/11/13
-	١	(positiv\$3 same dop\$3))	US-PGPUB;	17:50
		(postotyto samo dopyt)	EPO; JPO;	''''
			DERWENT	
_	l 0	5852311.pn. and ((p adj channel) or	USPAT;	2003/11/13
	Ĭ	(positiv\$3 same dop\$3))	US-PGPUB;	17:50
			EPO; JPO;	
			DERWENT	
-	0		USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB;	17:50
			EPO; JPO;	
		<u>'</u>	DERWENT	
-	0	6515328.pn. and ((p adj channel) or	USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB;	17:51
			EPO; JPO;	
		l coi coi c	DERWENT	2002/11/12
-	0		USPAT;	2003/11/13
		(positiv\$3 same dop\$3))	US-PGPUB;	17:51
			EPO; JPO;	
		CAECE3E mm and //n add shannel\ an	DERWENT	2003/11/13
_	1	6456535.pn. and ((p adj channel) or	USPAT; US-PGPUB;	17:51
	1	(positiv\$3 same dop\$3))	EPO; JPO;	17.31
1			DERWENT	
_	0	6261906.pn. and ((p adj channel) or	USPAT;	2003/11/13
	1	(positiv\$3 same dop\$3))	US-PGPUB;	17:55
	1	(hoptotata)	EPO; JPO;	
			DERWENT	]
L	1	<u> </u>	<u> </u>	<u> </u>

_	0	6372651.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:56
-	o	6383939.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:56
-	0	6515328.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:57
-	0	6316316.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:57
_	1	6456535.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:57
_	0	6249819.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:58
-	0	20030201477.pn. and ((p adj channel) or (positiv\$3 same dop\$3))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 17:58
_	0	438/264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/13 18:02
-	18	(control adj gate) and ((oxide adj layer) with ("50" adj angstroms)) and ((p adj channel) or (p-channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and	USPAT; US-PGPUB; EPO; JPO;	2003/11/25
_	303	((oxide adj layer) with ("50" adj angstroms)) and ((p-channel) or (p adj channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric	USPAT; US-PGPUB;	2003/11/13 18:10
_	3	adj layer) and (control adj gate) and ((p-channel) or (p adj channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and	EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/11/25 14:47
-	1	((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel)) 5408115.pn. and ((oxide adj layer) with ("40" adj angstroms)) and ((p-channel) or (p adj channel))	DERWENT  USPAT; US-PGPUB; EPO; JPO;	2003/11/25 14:18
_	13	(memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("30" adj	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/25 14:53
-	13	angstroms)) and ((p-channel) or (p adj channel)) (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and	USPAT; US-PGPUB; EPO; JPO;	2003/11/25 14:54
-	0	((oxide adj layer) with ("23" adj angstroms)) and ((p-channel) or (p adj channel)) 6515328.pn. and (p-channel or p adj channel)	USPAT; US-PGPUB; EPO; JPO;	2003/11/26 14:02
			DERWENT	

-	. 0	6372651.pn. and (p-channel or p adj channel)	USPAT; US-PGPUB;	2003/11/26 14:03
_	0	6383939.pn. and (p-channel or p adj	EPO; JPO; DERWENT USPAT;	2003/11/26
	Ŭ	channel)	US-PGPUB; EPO; JPO; DERWENT	14:04
_	0	6383939.pn. and (p-channel or p adj channel or p channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/26 14:04
	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17
-	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and (oxide adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/29 16:05
-	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17
-	0	438/257,263, 264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17
_	588	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17
-	7	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/22 12:01
-	3	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:15
-	1	6136652.pn. and (oxide same "40")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:12
-	1	angstroms)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17
-	0	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and ((p adj channel) or p-channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:16
_	3	438/257,263,264,762,763.ccls. and (memory adj cell) and (oxide adj layer) and (floating adj gate) and (dielectric adj layer) and (control adj gate) and ((oxide adj layer) with ("40" adj angstroms)) and @ad<20000228 and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/17 15:17

6				
-	1	438/257,263,264,762,763.ccls. and (memory	USPAT;	2004/04/17
		adj cell) and (oxide adj layer) and	US-PGPUB;	15:21
		(floating adj gate) and (dielectric adj	EPO; JPO;	
		layer) and (control adj gate) and ((oxide	DERWENT	
-		adj layer) with ("40" adj angstroms)) and		
		@ad<20000228 and (erase same volt\$3)		
-	1	6136652.pn. and (erase same volt\$3)	USPAT;	2004/04/17
			US-PGPUB;	15:23
			EPO; JPO;	
			DERWENT	
_	1	6136652.pn. and (erase same volt\$3 same	USPAT;	2004/04/17
		(floating adj gate))	US-PGPUB;	15:30
			EPO; JPO;	
			DERWENT	
_	0	6245613.pn. and (erase same volt\$3 same	USPAT;	2004/04/17
		(floating adj gate))	US-PGPUB;	15:30
			EPO; JPO;	
			DERWENT	
-	0	6246089.pn. and (erase same volt\$3 same	USPAT;	2004/04/17
		(floating adj gate))	US-PGPUB;	15:31
		(======================================	EPO; JPO;	
			DERWENT	
l _	2	6245613.PN.	USPAT;	2004/04/17
		<del></del>	US-PGPUB;	17:06
			EPO; JPO;	
			DERWENT	
1_	2	6297103.pn.	USPAT;	2004/10/21
	-	023/103.pm.	US-PGPUB;	15:27
			EPO; JPO;	
			DERWENT	
_	2	6456535.pn.	USPAT;	2004/10/21
		0430333.pm.	US-PGPUB;	15:34
		,	EPO; JPO;	
			DERWENT	
	3	6605961.pn.	USPAT;	2004/10/21
-	]	0003901.pii.	US-PGPUB;	15:36
1			EPO; JPO;	10.50
	ļ		DERWENT	
	2	6639835.pn.	USPAT;	2004/10/21
-		6639633.pii.	US-PGPUB;	15:38
			EPO; JPO;	10.00
į			DERWENT	
	ا م	6720221.pn.	USPAT;	2004/10/21
_	2	6/20221.pn.	US-PGPUB;	15:39
			EPO; JPO;	15.59
			DERWENT	
	_	6730060 mm	USPAT;	2004/10/21
-	2 .	6730960.pn.	•	15:52
1			US-PGPUB;	13.32
			EPO; JPO;	·
	_	6720060 mm and 1153 making 14 makin	DERWENT	2004/10/21
_	0	6730960.pn. and ((floating adj gate) same	USPAT;	2004/10/21
		(6605961.pn. adj volts) same erase)	US-PGPUB;	15:56
			EPO; JPO;	
			DERWENT	0004/10/01
-	0	6730960.pn. and ((floating adj gate) same	USPAT;	2004/10/21
	1	"3 volts")	US-PGPUB;	16:08
	1		EPO; JPO;	
			DERWENT	0004/10/01
-	0	6730960.pn. and ((floating adj gate) same	USPAT;	2004/10/21
	1	"<3 volts")	US-PGPUB;	16:11
	1		EPO; JPO;	·
			DERWENT	0004/10/01
-	10352	("<3 volts")	USPAT;	2004/10/21
	1	'	US-PGPUB;	16:10
	1		EPO; JPO;	
	1		DERWENT	
-	0	6730960.pn. and ((floating adj gate) same	USPAT;	2004/10/21
		"<3 volts" same erase)	US-PGPUB;	16:12
1			EPO; JPO;	1
			DERWENT	

		5500001	1163	·				1 0 0 0 4 / 1 0 / 0 1
<del>-</del>	0	6720221.pn. and		adj	gate)	same	USPAT;	2004/10/21
		"<3 volts" same	erase)				US-PGPUB;	16:13
							EPO; JPO;	
							DERWENT	•
-	0	6639835.pn. and	((floating	adj	gate)	same	USPAT;	2004/10/21
		"<3 volts" same	erase)	_			US-PGPUB;	16:14
							EPO; JPO;	
							DERWENT	
1 _	0	6605961.pn. and	((floating	adi	gate)	same	USPAT;	2004/10/21
	-	"<3 volts" same			J /		US-PGPUB;	16:14
		10 10105 54	orabo,				EPO; JPO;	
	,						DERWENT	
_	0	6456535.pn. and	((floating	adi	rate)	same	USPAT;	2004/10/21
-		"<3 volts" same		auj	gace,	Jane	US-PGPUB;	16:15
		3 VOICS Same	erase)				EPO; JPO;	10.13
							DERWENT	
		6207102	1157					2004/10/21
<del>-</del>	10	6297103.pn. and	•	adj	gate	Same	USPAT;	' ' '
		"<3 volts" same	erase)				US-PGPUB;	16:15
							EPO; JPO;	
							DERWENT	